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Title:Plasmonic detection of terahertz radiation in two-dimension channel of double-grating-gate field-effect transistors with asymmetric unit cell

Authors:Fateev, D.V. (1); Popov, V.V. (1); Otsuji, T.; Meziani, Y.M. (2); Coquillat, D. (3); Knap, V. (3); Nikitov, S.A. (4)

Author affiliation:(1) Saratov Div., Kotelnikov Inst. of Radio Eng. & Electron., Saratov, Russia; (2) Univ. of Salamanca, Salamanca, Spain; (3) Univ. of Montpellier 2, Montpellier, France; (4) Kotelnikov Inst. of Radio Eng. & Electron., Moscow, Russia

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Abstract:We propose the field-effect transistor structure with two-dimension electron channel and double grating gate with asymmetric unit cell for plasmonic terahertz detection.

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